EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	1	11/898583	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/05/19 12:44
S2	1	10/596573	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/05/19 12:45
S3	41395	BiCMOS or (bipolar same (FET or (field near effect near transistor)))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/05/19 13:13
S4	65714	passivation near (layer$1 or film$1)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/05/19 13:13
S5	273227	(contact or conductor or electrode) near (plug$1 or hole$1 or via$1 or through-hole$1 or (through near hole$1))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/05/19 13:13
S6	513333	(wiring or metal or conductor) near (layer $1 or film$1)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/05/19 13:14
S7	766	S3 and S4 and S5 and S6	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/05/19 13:45
S8	670	(257/370).CCLS.	US-PGPUB; USPAT; USOCR	OR	OFF	2009/05/19 13:46
S9	635	(257/378).CCLS.	US-PGPUB; USPAT; USOCR	OR	OFF	2009/05/19 13:46
S10	4369	(257/758).CCLS.	US-PGPUB; USPAT; USOCR	OR	OFF	2009/05/19 13:47
S11	3323	(257/774).CCLS.	US-PGPUB; USPAT; USOCR	OR	OFF	2009/05/19 13:47
S12	847	(257/775).CCLS.	US-PGPUB; USPAT; USOCR	OR	OFF	2009/05/19 13:47

S13	866	(257/776).CCLS.	US-PGPUB; USPAT; USOCR	OR	OFF	2009/05/19 13:47
S14	38	(257/E27.109).CCLS.	US-PGPUB; USPAT; USOCR	OR	OFF	2009/05/19 13:47
S15	53	(257/E29.221).CCLS.	US-PGPUB; USPAT; USOCR	OR	OFF	2009/05/19 13:47
S16	128	(257/E25.01).CCLS.	US-PGPUB; USPAT; USOCR	OR	OFF	2009/05/19 13:48
S17	1040	(257/E25.011).CCLS.	US-PGPUB; USPAT; USOCR	OR	OFF	2009/05/19 13:48
S18	25	(257/E25.014).CCLS.	US-PGPUB; USPAT; USOCR	OR	OFF	2009/05/19 13:48
S19	708	(257/E25.016).CCLS.	US-PGPUB; USPAT; USOCR	OR	OFF	2009/05/19 13:48
S20	47	(257/E25.024).CCLS.	US-PGPUB; USPAT; USOCR	OR	OFF	2009/05/19 13:49
S21	180	(257/E25.026).CCLS.	US-PGPUB; USPAT; USOCR	OR	OFF	2009/05/19 13:49
S22	2020	(257/E23.145).CCLS.	US-PGPUB; USPAT; USOCR	OR	OFF	2009/05/19 13:49
S23	5	US-4933297-$.DID. OR US-5563433-$.DID. OR US-5714793-$.DID. OR US-6157068-$.DID. OR US-20020050627-$.DID. OR DE-20030327-$.DID.	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/05/19 13:50
S24	1	US-20020104995-$.DID.	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/05/19 13:50
S25	85	((ZHONG-XIANG) near2 (HE)).INV.	US-PGPUB; USPAT	ADJ	ON	2009/05/19 13:54
S26	20	((BRADLEY) near2 (ORNER)).INV.	US-PGPUB; USPAT	ADJ	ON	2009/05/19 13:54
S27	37	((VIDHYA) near2 (RAMACHANDRAN)).INV.	US-PGPUB; USPAT	ADJ	ON	2009/05/19 13:54
S28	59	((ALVIN) near2 (JOSEPH)).INV.	US-PGPUB; USPAT	ADJ	ON	2009/05/19 13:54
S29	44	((STEPHEN) near2 ("ST ONGE")).INV.	US-PGPUB; USPAT	ADJ	ON	2009/05/19 13:55
S30	63	((PING-CHUAN) near2 (WANG)).INV.	US-PGPUB; USPAT	ADJ	ON	2009/05/19 13:55
S31	0	("23or24or25or26or27or28").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2009/05/19 13:58
S32	269	S25 or S26 or S27 or S28 or S29 or S30	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/05/19 13:59
S33	2	("2002/0076874").URPN.	USPAT	ADJ	ON	2009/05/19 14:34
S34	41395	BiCMOS or (bipolar same (FET or (field near effect near transistor)))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/05/19 19:28

S35	65714	passivation near (layer$1 or film$1)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/05/19 19:28
S36	273227	(contact or conductor or electrode) near (plug$1 or hole$1 or via$1 or through-hole$1 or (through near hole$1))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/05/19 19:28
S37	513333	(wiring or metal or conductor) near (layer $1 or film$1)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/05/19 19:28
S38	766	S34 and S35 and S36 and S37	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/05/19 19:28
S39	698	S38 and (@pd< = "20031216" or @ad< = "20031216" or @rlad< = "20031216")	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/05/19 19:28
S40	670	(257/370).CCLS.	US-PGPUB; USPAT; USOCR	OR	OFF	2009/05/19 20:56
S41	635	(257/378).CCLS.	US-PGPUB; USPAT; USOCR	OR	OFF	2009/05/19 20:56
S42	4369	(257/758).CCLS.	US-PGPUB; USPAT; USOCR	OR	OFF	2009/05/19 20:56
S43	3323	(257/774).CCLS.	US-PGPUB; USPAT; USOCR	OR	OFF	2009/05/19 20:56
S44	847	(257/775).CCLS.	US-PGPUB; USPAT; USOCR	OR	OFF	2009/05/19 20:56
S45	866	(257/776).CCLS.	US-PGPUB; USPAT; USOCR	OR	OFF	2009/05/19 20:56
S46	38	(257/E27.109).CCLS.	US-PGPUB; USPAT; USOCR	OR	OFF	2009/05/19 20:56
S47	53	(257/E29.221).CCLS.	US-PGPUB; USPAT; USOCR	OR	OFF	2009/05/19 20:56
S48	128	(257/E25.01).CCLS.	US-PGPUB; USPAT; USOCR	OR	OFF	2009/05/19 20:56
S49	1040	(257/E25.011).CCLS.	US-PGPUB; USPAT; USOCR	OR	OFF	2009/05/19 20:56
S50	708	(257/E25.016).CCLS.	US-PGPUB; USPAT; USOCR	OR	OFF	2009/05/19 20:56
S51	47	(257/E25.024).CCLS.	US-PGPUB; USPAT; USOCR	OR	OFF	2009/05/19 20:56
S52	180	(257/E25.026).CCLS.	US-PGPUB; USPAT; USOCR	OR	OFF	2009/05/19 20:56

S53	2020	(257/ E23.145).CCLS.	US-PGPUB; USPAT; USOCR	OR	OFF	2009/05/19 20:56
S54	12350	S40 or S41 or S42 or S43 or S44 or S45 or S46 or S47 or S48 or S49 or S50 or S51 or S52 or S53	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/05/19 20:56
S55	9556	S54 and (@pd<="20031216" or @ad<="20031216" or @rlad<="20031216")	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/05/19 20:56
S56	952	S55 and (BiCMOS or (bipolar same (FET or (field near effect near transistor))))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/05/19 20:56
S57	1398	S55 and (passivation near (layer$1 or film $1))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/05/19 20:56
S58	3784	S55 and ((contact or conductor or electrode) near (plug$1 or hole$1 or via $1 or through-hole$1 or (through near hole$1)))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/05/19 20:57
S59	5670	S55 and ((wiring or metal or conductor) near (layer$1 or film$1))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/05/19 20:57
S60	48	S56 and S57 and S58 and S59	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/05/19 20:58
S61	378	multi near2 (layer$1 or level) near2 metal near2 interconnect	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/05/19 21:03
S62	317	S61 and (@pd<="20031216" or @ad<="20031216" or @rlad<="20031216")	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/05/19 21:03

S63	471	vertical near2 bipolar same (fet or (field near effect near transistor))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/05/19 21:28
S64	420	S63 and (@pd<="20031216" or @ad<="20031216" or @rlad<="20031216")	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/05/19 21:28
S65	3289	vertical near2 bipolar	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/05/19 21:37
S66	2744	S65 and (@pd<="20031216" or @ad<="20031216" or @rlad<="20031216")	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/05/19 21:37
S67	738	S66 and mosfet	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/05/19 21:37
S68	531	S67 not S64	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/05/19 21:37
S69	531	S68 not S62	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/05/19 21:37
S70	527	S68 not S39	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/05/19 21:38
S71	527	S70 not S60	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/05/19 21:38
S72	0	("2009/0039522").URPN.	USPAT	ADJ	ON	2009/05/19 21:47
S73	0	("2009/0039522").URPN.	USPAT	ADJ	ON	2009/05/19 21:47

S74	1	("20090050971").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2009/05/20 10:08
S75	0	11/958773	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/05/20 11:03
S76	0	("11958773").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2009/05/20 11:03
S77	0	(11/840604).CCLS.	US-PGPUB; USPAT; USOCR	OR	OFF	2009/05/20 20:33
S78	1	11/840604	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/05/20 20:33
S79	1	11/523566	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/05/20 20:59
S80	14	("6399993").URPN.	USPAT	ADJ	ON	2009/05/21 13:20
S81	7	("6979884").URPN.	USPAT	ADJ	ON	2009/05/21 13:22
S82	0	("7534679").URPN.	USPAT	ADJ	ON	2009/05/21 13:23
S83	0	("7466010").URPN.	USPAT	ADJ	ON	2009/05/21 13:23
S84	0	10/596573	USPAT	ADJ	ON	2009/05/21 13:27
S85	1	10/596573	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/05/21 13:27

5/21/2009 4:14:25 PM
C:\ Documents and Settings\ vsengdara\ My Documents\ EAST\ Workspaces\ 10596573 BIPOLAR AND CMOS INTEGRATION WITH REDUCED CONTACT HEIGHT.wsp